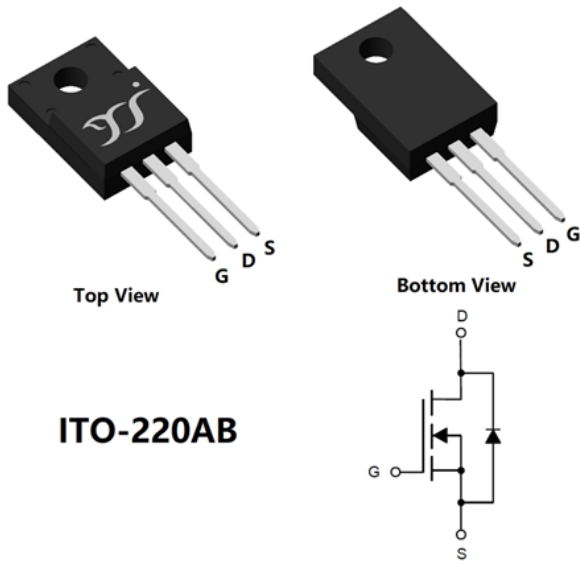


N-Channel Enhancement Mode Field Effect Transistor



Product Summary

- V_{DS} 650V
- I_D 10.5A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) <math>< 190m\Omega</math>
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power switching application
- Uninterruptible power supply
- DC-DC convertor

Limiting Values

Parameter	Conditions	Symbol	Min	Max	Unit		
Drain-source Voltage		V_{DS}	-	650	V		
Gate-source Voltage		V_{GS}	-30	30			
Continuous Drain Current (Note 1,2)	Steady-State	I_D	$T_A=25^\circ C, V_{GS}=10V$	-	2	A	
			$T_A=100^\circ C, V_{GS}=10V$	-	1.2		
Continuous Drain Current (Note 1,3)	Steady-State		$T_C=25^\circ C, V_{GS}=10V, \text{Chip limitation}$	-	10.5		
			$T_C=100^\circ C, V_{GS}=10V$	-	6.6		
Pulsed Drain Current	$T_C=25^\circ C, t_p \leq 10\mu s$	I_{DM}	-	42			
Maximum Body-Diode Continuous Current	$T_C=25^\circ C$	I_S	-	10.5			
Maximum Body-Diode Pulsed Current	$T_C=25^\circ C, t_p \leq 10\mu s$	I_{SM}	-	42			
Avalanche Energy (non-repetitive)	$T_J=25^\circ C, V_G=10V, R_G=25\Omega, L=30mH, I_{AS}=4.19A$	EAS	-	263.34	mJ		
Total Power Dissipation (Note 1,2)	Steady-State	P_D	$T_A=25^\circ C$	-	1.95	W	
			$T_A=100^\circ C$	-	0.78		
Total Power Dissipation (Note 1,3)	Steady-State		$T_C=25^\circ C$	-	54		
			$T_C=100^\circ C$	-	21		
Insulation withstand voltage	Vrms, t=60s		V_{ISO}	-	3		KV
Junction and Storage Temperature Range			T_J, T_{STG}	-55	150		$^\circ C$

Thermal Resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{\theta JA}$	-	64	$^\circ C/W$
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	2.3	

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJF190C65BHJ	B1	YJF190C65B	50	/	5000	Tube



YJF190C65BHJ

■ Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A, T_J=25^\circ C$	650	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=650V, V_{GS}=0V, T_J=25^\circ C$	-	-	1	μA
		$V_{DS}=650V, V_{GS}=0V, T_J=150^\circ C$	-	-	100	
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V, T_J=25^\circ C$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A, T_J=25^\circ C$	2	2.8	3.6	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=10A, T_J=25^\circ C$	-	153	190	m Ω
		$V_{GS}=10V, I_D=10A, T_J=150^\circ C$	-	390	485	
Diode Forward Voltage	V_{SD}	$I_S=10.5A, V_{GS}=0V, T_J=25^\circ C$	-	0.85	1.2	V
Gate Resistance	R_G	$f=1MHz, T_J=25^\circ C$	-	5.2	-	Ω
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=325V, V_{GS}=0V, f=1MHz, T_J=25^\circ C$	-	1250	-	pF
Output Capacitance	C_{oss}		-	30	-	
Reverse Transfer Capacitance	C_{riss}		-	2.5	-	
Effective Output capacitance, Energy Related	$C_{o(er)}$	$V_{DS}=0\dots 325V, V_{GS}=0V, f=1MHz, T_J=25^\circ C$	-	56	-	
Effective Output Capacitance, Time Related	$C_{o(tr)}$		-	330	-	
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=325V, I_D=10A, T_J=25^\circ C$	-	25	-	nC
Gate-Source Charge	Q_{gs}		-	5.1	-	
Gate-Drain Charge	Q_{gd}		-	8.6	-	
Reverse Recovery Charge	Q_{rr}	$I_F=10A, di/dt=100A/\mu s, V_{GS}=0V, V_R=325V, T_J=25^\circ C$	-	2780	-	nC
Reverse Recovery Time	t_{rr}		-	221	-	ns
Peak Reverse Recovery Current	I_{rm}		-	26.7	-	A
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=325V, I_D=10A, R_{GEN}=3\Omega, T_J=25^\circ C$	-	22	-	ns
Turn-on Rise Time	t_r		-	19.4	-	
Turn-off Delay Time	$t_{D(off)}$		-	33	-	
Turn-off Fall Time	t_f		-	12.3	-	

Note:

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. The value of $R_{\theta JA}$ is measured in the still air environment with $T_A=25^\circ C$. The maximum allowed junction temperature of $150^\circ C$.
3. Thermal resistance from junction to soldering point (on the exposed drain pad).



Typical Electrical and Thermal Characteristics Diagrams

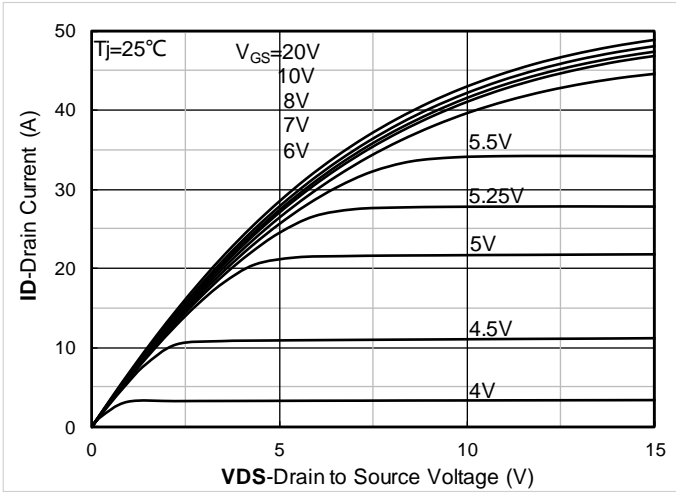


Figure 1. Output Characteristics; typical values

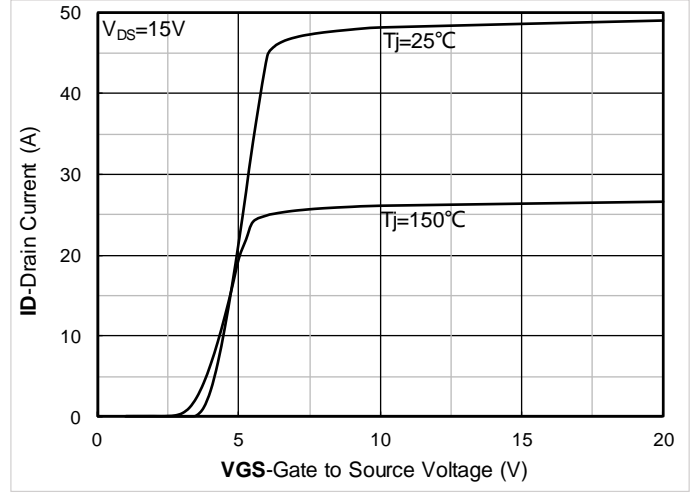


Figure 2. Transfer Characteristics; typical values

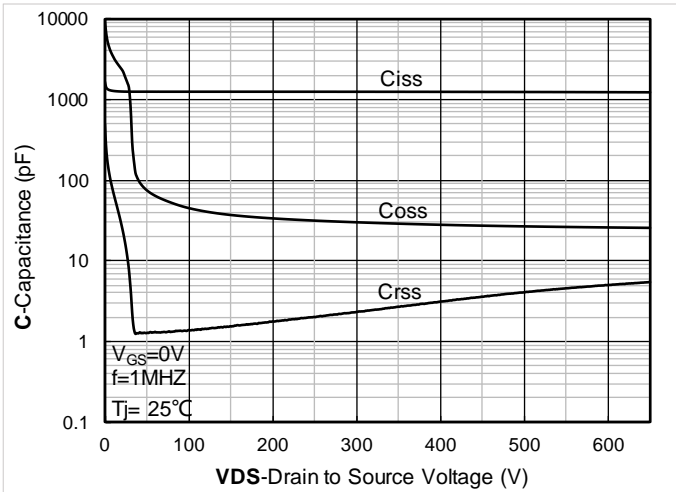


Figure 3. Capacitance Characteristics; typical values

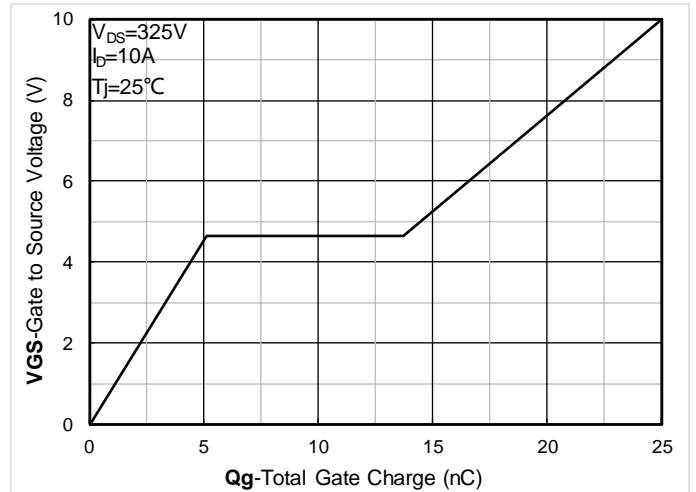


Figure 4. Gate Charge; typical values

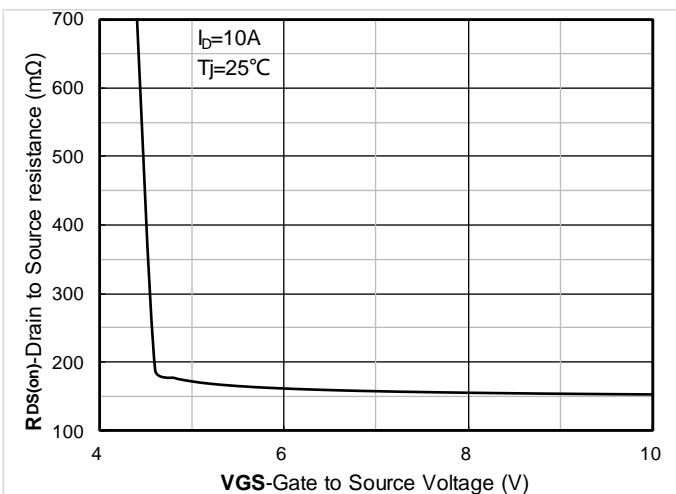


Figure 5. On-Resistance vs. Gate to Source Voltage; typical values

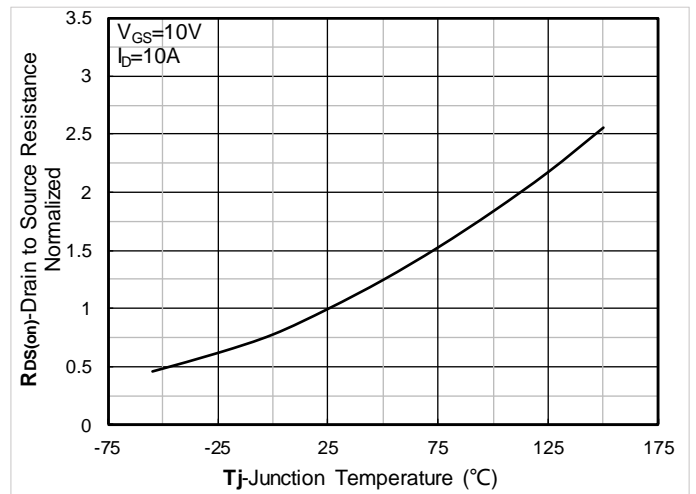


Figure 6. Normalized On-Resistance



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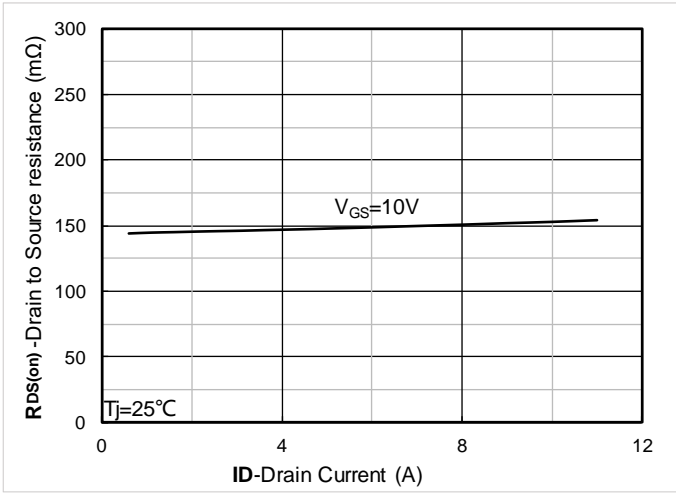


Figure 7. RDS(on) vs. Drain Current; typical values

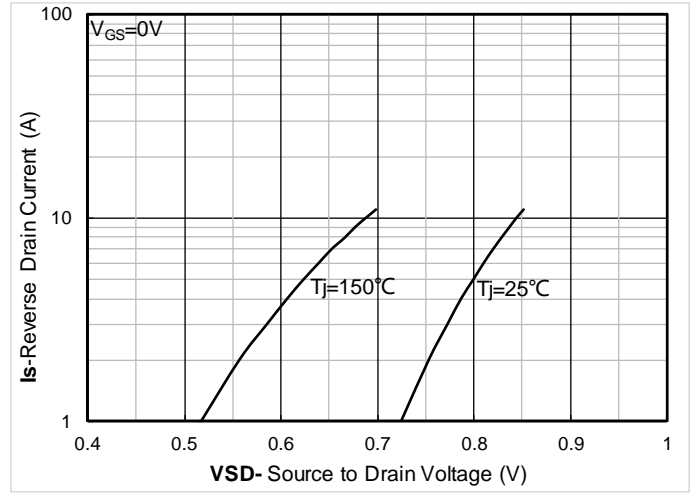


Figure 8. Forward characteristics of reverse diode; typical values

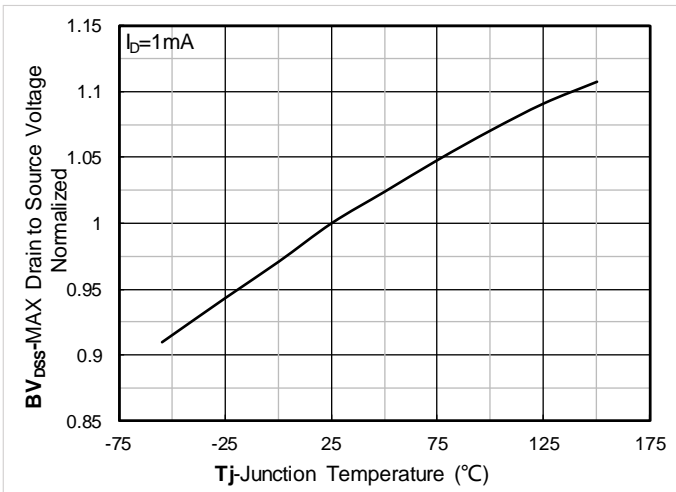


Figure 9. Normalized breakdown voltage

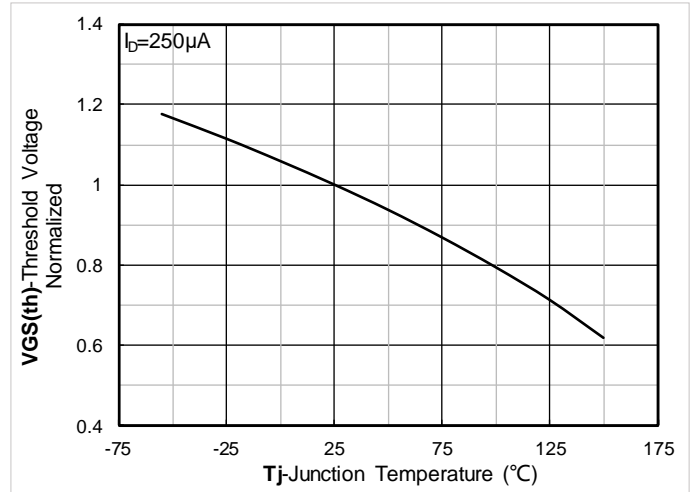


Figure 10. Normalized Threshold voltage

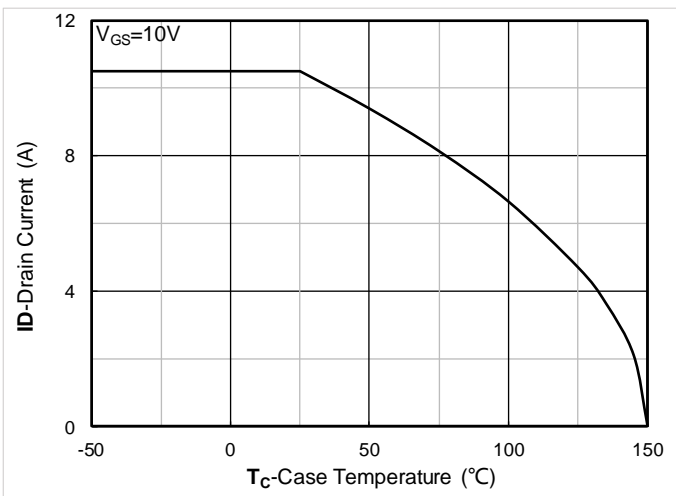


Figure 11. Current dissipation

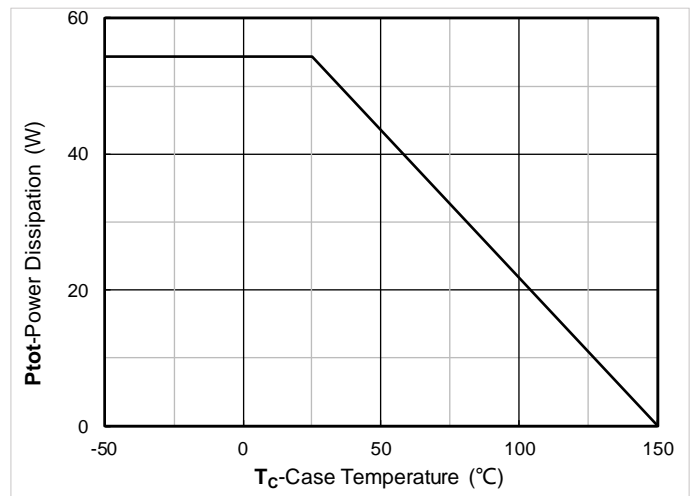


Figure 12. Power dissipation



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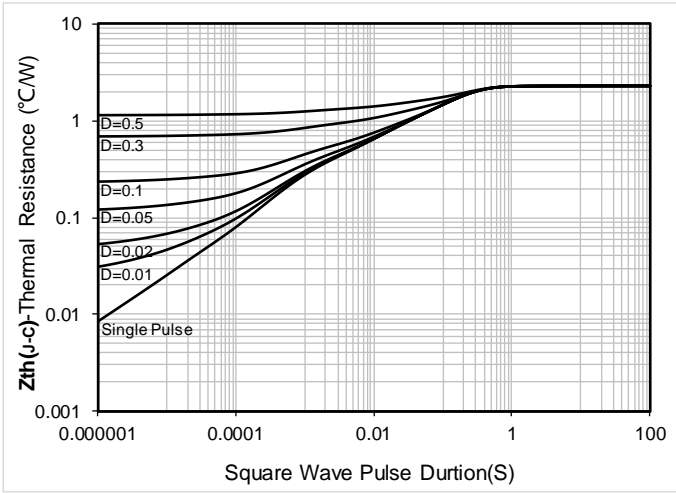


Figure 13. Maximum Transient Thermal Impedance

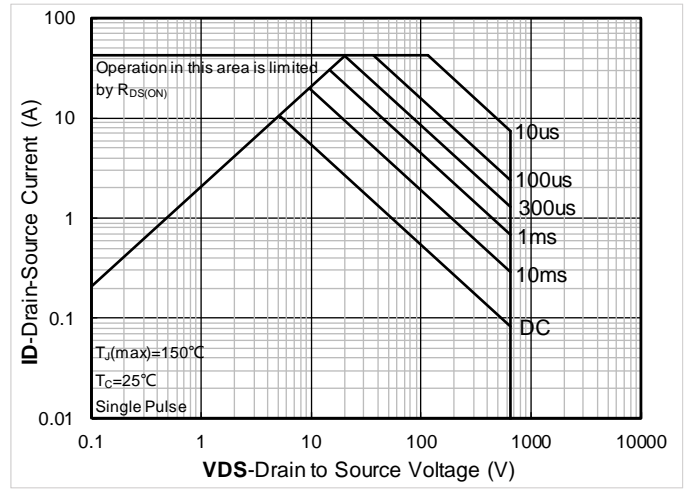


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

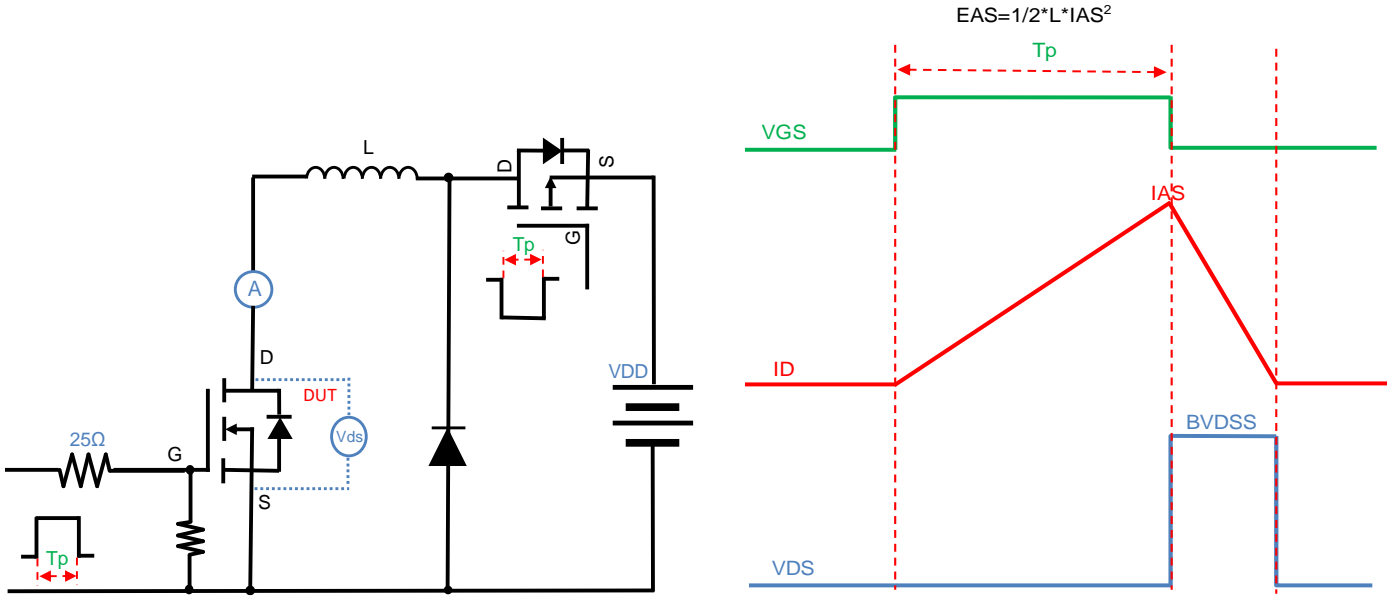


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

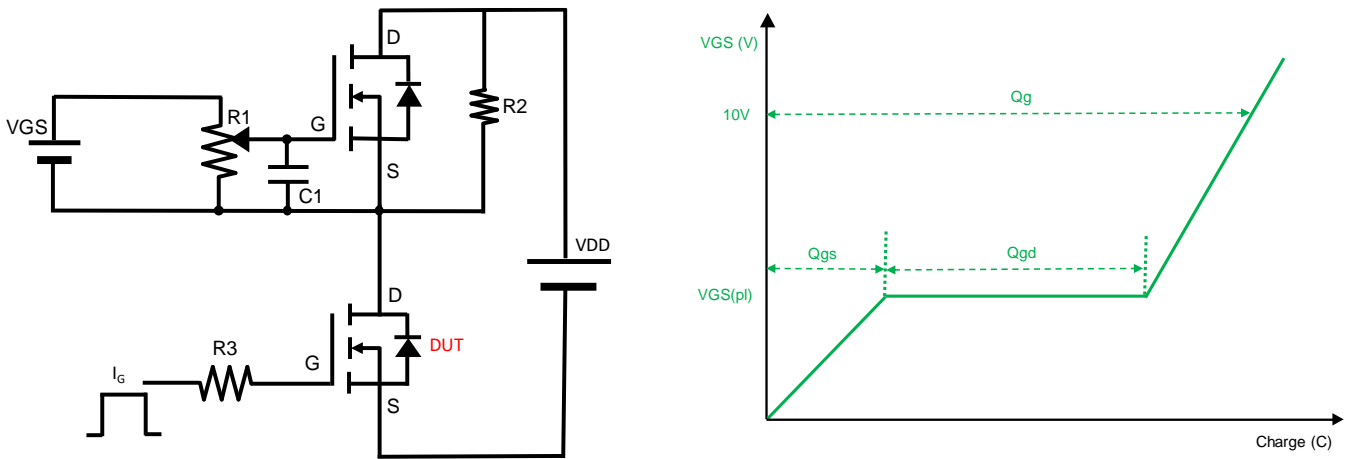


Figure B. Gate Charge Test Circuit & Waveform

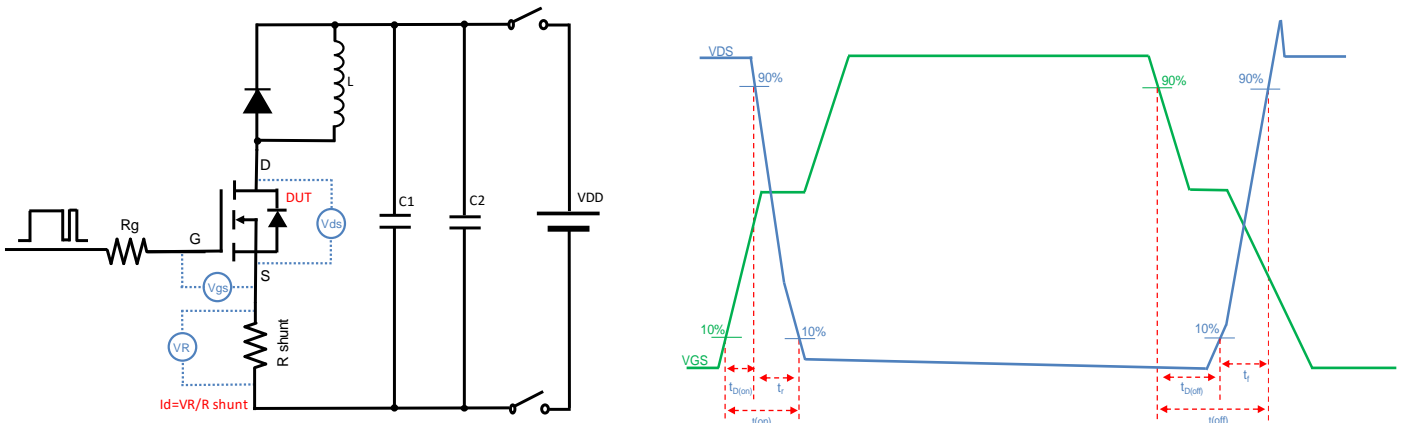


Figure C. Resistive Switching Test Circuit & Waveform

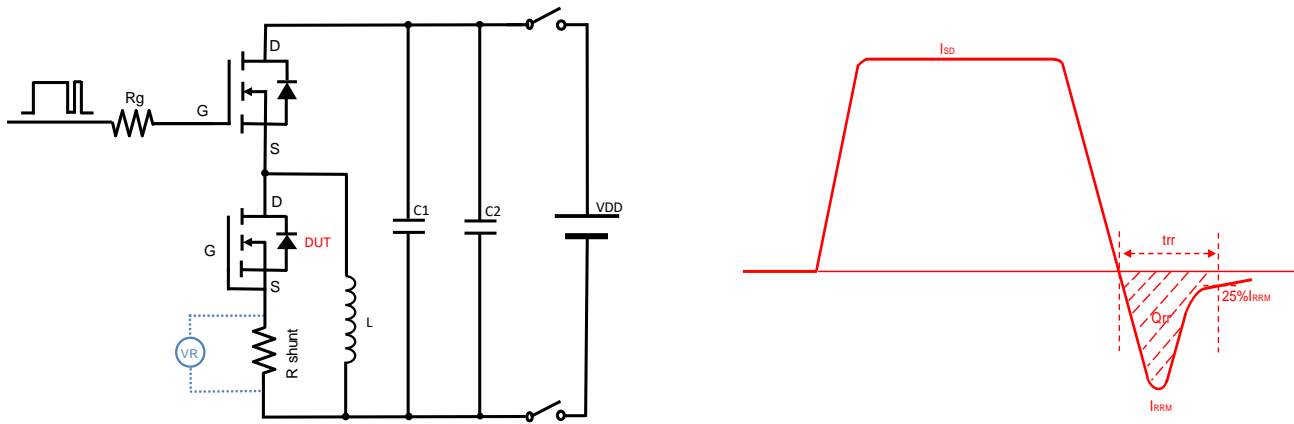
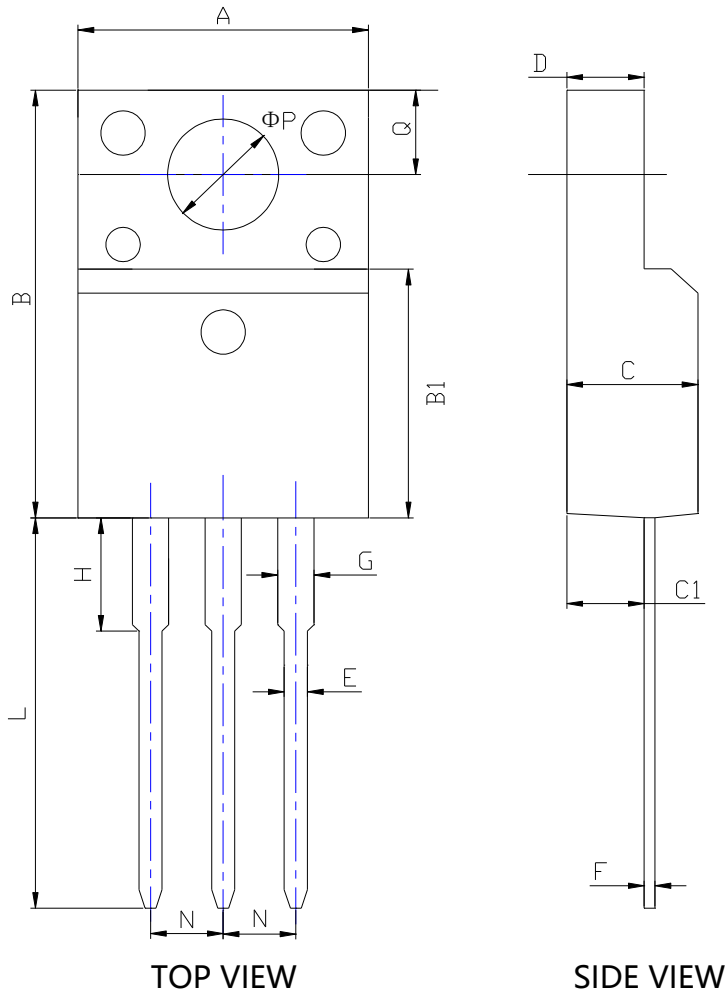


Figure D. Diode Recovery Test Circuit & Waveform



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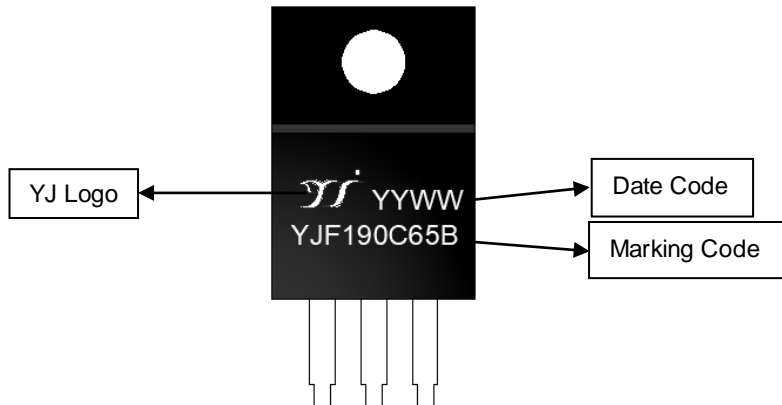
■ ITO-220AB-C Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.382	0.406	9.700	10.300
B	0.610	0.634	15.500	16.100
B1	0.354	0.370	8.990	9.390
C	0.177	0.193	4.500	4.900
C1	0.102	0.116	2.600	2.950
D	0.092	0.108	2.340	2.740
E	0.028	0.035	0.700	0.900
F	0.016	0.024	0.400	0.600
G	0.044	0.056	1.120	1.420
H	0.106	0.126	2.700	3.200
L	0.496	0.535	12.600	13.600
N	0.092	0.108	2.340	2.740
Q	0.124	0.140	3.150	3.550
ΦP	0.118	0.130	3.000	3.300

NOTE:
 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.

■ Marking Information



Note:

1. All marking is at middle of the product body
2. All marking is in laser printing
3. YJF190C65B is marking code, YYWW is date code, "YY" is year, "WW" is week
4. Body color: Black



YJF190C65BHJ

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